

STRUCTURE Silicon Monolithic Integrated Circuit

NAME OF PRODUCT DC-AC Inverter Control IC

TYPE BD9888F, BD9888FV

FUNCTION

- · 2ch control with Push-Pull
- · Lamp current and voltage sense feed back control
- · Sequencing easily achieved with Soft Start Control
- Short circuit protection with Timer Latch
- Under Voltage Lock Out
- Short circuit protection with over voltage
- Mode-selectable the operating or stand-by mode by stand-by pin
- Synchronous operating the other BD9888F or BD9888FV IC's
- BURST mode controlled by PWM and DC input
- Short circuit protection with voltage difference detection

OAbsolute Maximum Ratings ($Ta = 25^{\circ}C$)

Parameter	Symbol	Limits	Unit	
Supply Voltage	Vcc	15	٧	
perating Temperature Range Topr		-40∼+90	°C	
Storage Temperature Range	Tstg	−55 ~ +125	°C	
Dower Dissipation	Pd	600*1 (BD9888F)	mW	
Power Dissipation		850*2 (BD9888FV)] ""	
Maximum Junction Temperature	Tjmax	+125	°C	

^{*1}Pd derate at 6.0mW/°C for temperature above Ta = 25°C (When mounted on a PCB 70.0mm×70.0mm×1.6mm)

ORecommended operating condition

Parameter	Symbol	Limits	Unit
Supply voltage	Vcc	5. 0~14. 0	٧
CT oscillation frequency	fCT	20~150	kHz
BCT oscillation frequency	fBCT	0.05~0.50	kHz

Status of this document

The Japanese version of this document is the official specification.

Please use the translation version of this document as a reference to expedite understanding of the official version. If these are any uncertainty in translation version of this document, official version takes priority.

 $^{^{*2}}$ Pd derate at 8.5mW/°C for temperature above Ta = 25°C (When mounted on a PCB 70.0mm×70.0mm×1.6mm)



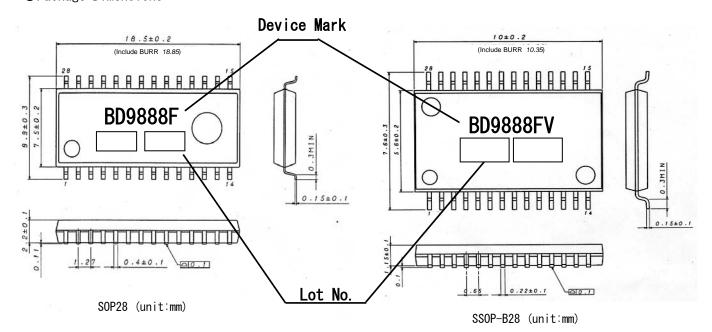
OElectric Characteristics (Ta=25°C, VCC=7V)

F
F
3CT=0. 050 μ I
S=0. 5V
n A
1 OmA
n A
1 OmA
CT=395pF
n

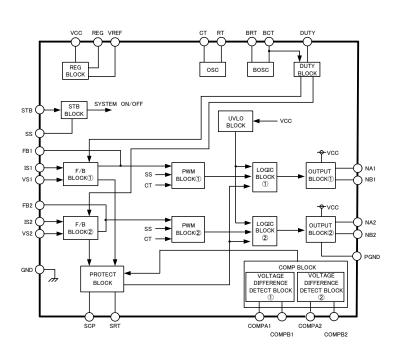
(This product is not designed to be radiation-resistant.)



OPackage Dimensions



OBlock Diagram



OPin Description

Pin No.	Pin Name	Function		
1	DUTY	Control PWM mode and BURST mode		
2	BRT	External resistor from BRT to GND for adjusting the BURST triangle oscillator		
3	ВСТ	External capacitor from BCT to GND for adjusting the BURST triangle oscillator		
4	RT	External resistor from SRT to RT for adjusting the triangle oscillator		
5	SRT	External resistor from SRT to RT for adjusting the triangle oscillator		
6	CT	External capacitor from CT to GND for adjusting the triangle oscillator		
7	GND	GROUND		
8	FB1	Error amplifier output①		
9	IS1	Error amplifier input①		
10	VS1	Error amplifier input②		
11	FB2	Error amplifier output②		
12	182	Error amplifier input③		
13	VS2	Error amplifier input(4)		
14	VREF	Reference voltage		
15	COMPA1	Voltage difference or under voltage detect for 1ch		
16	STB	Stand-by switch		
17	COMPB1	Voltage difference or under voltage detect for 1ch		
18	COMPA2	Voltage difference or under voltage detect for 2ch		
19	COMPB2	Voltage difference or under voltage detect for 2ch.		
20	REG	Internal regulator output		
21	SS	External capacitor from SS to GND for Soft Start Control		
22	SCP	External capacitor from SCP to GND for Timer Latch		
23	NA2	FET driver for 2ch		
24	NB2	FET driver for 2ch		
25	PGND	Ground for FET drivers		
26	NB1	FET driver for 1ch		
27	NA1	FET driver for 1ch		
28	Vcc	Supply voltage input		



ONOTE FOR USE

- 1. When designing the external circuit, including adequate margins for variation between external devices and IC. Use adequate margins for steady state and transient characteristics.
- 2. The circuit functionality is guaranteed within of ambient temperature operation range as long as it is within recommended operating range. The standard electrical characteristic values cannot be guaranteed at other voltages in the operating ranges, however the variation will be small.
- 3. Mounting failures, such as misdirection or miscounts, may harm the device.
- 4. A strong electromagnetic field may cause the IC to malfunction.
- 5. The GND pin should be the location within $\pm 0.3V$ compared with the PGND pin.
- 6. BD9888F and BD9888FV incorporate a built-in thermal shutdown circuit (TSD circuit). The thermal shutdown circuit (TSD circuit) is designed only to shut the IC off to prevent runaway thermal operation. It is not designed to protect the IC or guarantee its operation of the thermal shutdown circuit is assumed.
- 7. Absolute maximum ratings are those values that, if exceeded, may cause the life of a device to become significantly shortened. Moreover, the exact failure mode caused by short or open is not defined. Physical countermeasures, such as a fuse, need to be considered when using a device beyond its maximum ratings.
- 8. About the external FET, the parasitic Capacitor may cause the gate voltage to change, when the drain voltage is switching. Make sure to leave adequate margin for this IC variation.
- 9. On operating Slow Start Control (SS is less than 2.2V), It does not operate Timer Latch.
- 1 O. By STB voltage, BD9888F and BD9888FV are changed to 2 states. Therefore, do not input STB pin voltage between one state and the other state $(0.8 \sim 1.6)$.
- 1 1. The pin connected a connector need to connect to the resistor for electrical surge destruction. This IC is a monolithic IC which (as shown is Fig-1) has P⁺ substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows.
 - \bigcirc (When GND > PinB and GND > PinA, the P-N junction operates as a parasitic diode.)
 - \bigcirc (When PinB > GND > PinA, the P-N junction operates as a parasitic transistor.)

Parasitic diodes can occur inevitably in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits as well as operation faults and physical damage. Accordingly you must not use methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin.

- 1 2. This IC is a monolithic IC which (as shown is Fig-1)has P⁺ substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows,
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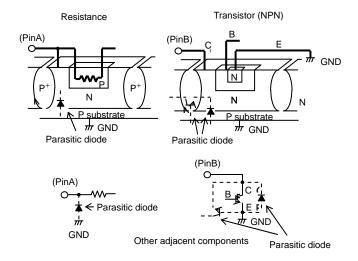


Fig-1 Simplified structure of a Bipolar IC

Notes

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